

FDWS86068-F085

N-Channel POWERTRENCH® MOSFET

100 V, 80 A, 6.4 mΩ

Features

- Typ $R_{DS(on)}$ = 5.2 mΩ at $V_{GS} = 10$ V, $I_D = 80$ A
- Typ $Q_{g(tot)}$ = 31 nC at $V_{GS} = 10$ V, $I_D = 80$ A
- UIS Capability
- Qualified to AEC Q101
- Wettable flanks for automatic optical inspection (AOI)
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Steering

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, Unless otherwise specified)

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain to Source Voltage	100	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current ($T_C = 25^\circ\text{C}$) Continuous ($V_{GS} = 10$ V) (Note 1) Pulsed	80 (see Fig. 4)	A
E_{AS}	Single Pulse Avalanche Energy (Note 2)	36	mJ
P_D	Power Dissipation Derate above 25°C	214 1.43	W W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to +150	$^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance (Junction to case)	0.7	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Maximum Thermal Resistance (Junction to Ambient) (Note 3)	50	$^\circ\text{C}/\text{W}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

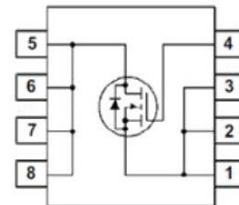


ON Semiconductor®

www.onsemi.com

V_{DSS}	I_D MAX	$R_{DS(on)}$ MAX
100 V	80 A	6.4 mΩ

ELECTRICAL CONNECTION

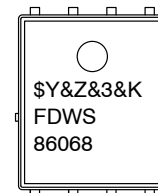


N-Channel MOSFET



Power 56
(DFN8)
CASE 506DW

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &3 = Numeric Date Code
 &K = Lot Code
 FDWS86068 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDWS86068–F085

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDWS86068	FDWS86068–F085	Power 56	13"	12 mm	3,000 Units

NOTES:

- Current is limited by wirebond configuration.
- Starting $T_J = 25^\circ\text{C}$, $L = 20\ \mu\text{H}$, $I_{AS} = 60\ \text{A}$, $V_{DD} = 80\ \text{V}$ during inductor charging and $V_{DD} = 0\ \text{V}$ during time in avalanche.
- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 in2 pad of 2oz copper.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

$B_{V_{DSS}}$	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$	100	–	–	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS} = 100\ \text{V}$, $V_{GS} = 0\ \text{V}$ ($T_J = 25^\circ\text{C}$) ($T_J = 175^\circ\text{C}$) (Note 4)	–	–	1	μA mA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\ \text{V}$	–	–	± 100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\ \text{V}$, $I_D = 80\ \text{A}$ ($T_J = 25^\circ\text{C}$) ($T_J = 175^\circ\text{C}$) (Note 4)	–	5.2 11.4	6.4 14	$\text{m}\Omega$

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 50\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	–	2220	–	pF
C_{oss}	Output Capacitance		–	1350	–	pF
C_{rss}	Reverse Transfer Capacitance		–	19	–	pF
R_g	Gate Resistance	$V_{GS} = 0.5\ \text{V}$, $f = 1\ \text{MHz}$	–	0.3	–	Ω
$Q_{g(tot)}$	Total Gate Charge	$V_{GS} = 0\ \text{to}\ 10\ \text{V}$, $V_{DD} = 50\ \text{V}$, $I_D = 80\ \text{A}$	–	31	43	nC
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0\ \text{to}\ 2\ \text{V}$, $V_{DD} = 50\ \text{V}$, $I_D = 80\ \text{A}$	–	4	–	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 50\ \text{V}$, $I_D = 80\ \text{A}$	–	12	–	nC
Q_{gd}	Gate to Drain "Miller" Charge		–	7	–	nC

SWITCHING CHARACTERISTICS

t_{on}	Turn-On Time	$V_{DD} = 50\ \text{V}$, $I_D = 80\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_{GEN} = 6\ \Omega$	–	–	30	ns
$t_{d(on)}$	Turn-On Delay Time		–	15	–	ns
t_r	Turn-On Rise Time		–	6	–	ns
$t_{d(off)}$	Turn-Off Delay Time		–	24	–	ns
t_f	Turn-Off Fall Time		–	7	–	ns
t_{off}	Turn-Off Time		–	–	48	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Source to Drain Diode Forward Voltage	$I_{SD} = 80\ \text{A}$, $V_{GS} = 0\ \text{V}$	–	0.95	1.3	V
		$I_{SD} = 40\ \text{A}$, $V_{GS} = 0\ \text{V}$	–	0.87	1.2	V
T_{rr}	Reverse Recovery Time	$I_F = 80\ \text{A}$, $dI_{SD}/dt = 100\ \text{A}/\mu\text{s}$	–	61	80	ns
Q_{rr}	Reverse Recovery Charge		–	56	84	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- The maximum value is specified by design at $T_J = 175^\circ\text{C}$. Product is not tested to this condition in production

TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

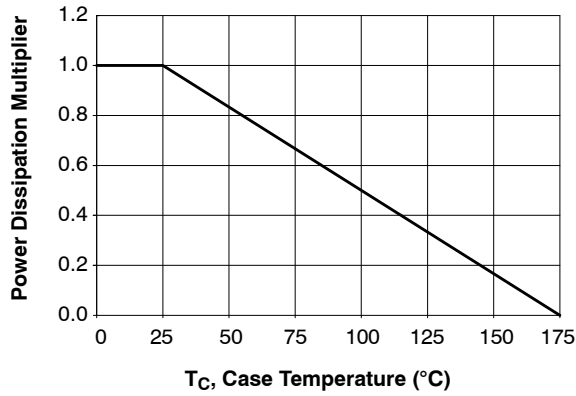


Figure 1. Normalized Power Dissipation vs. Case Temperature

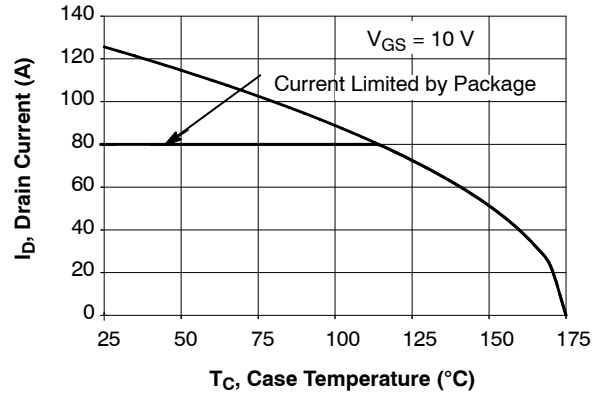


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

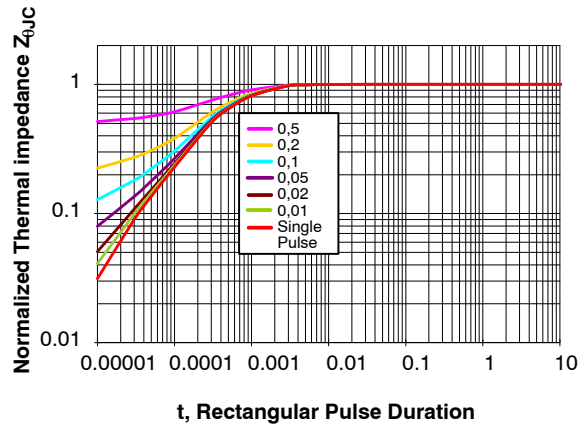


Figure 3. Normalized Maximum Transient Thermal Impedance

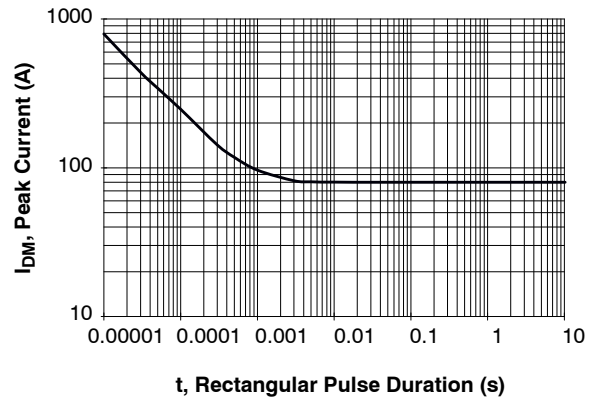


Figure 4. Peak Current Capability

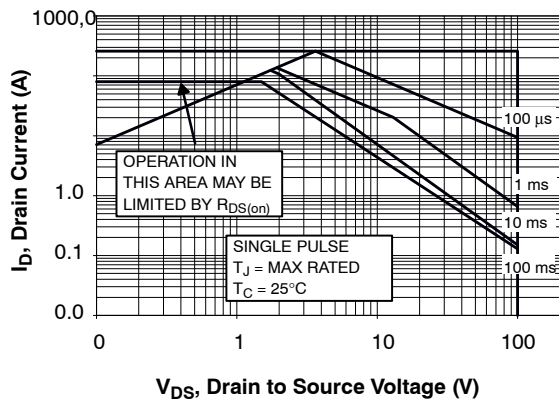


Figure 5. Forward Bias Safe Operating Area

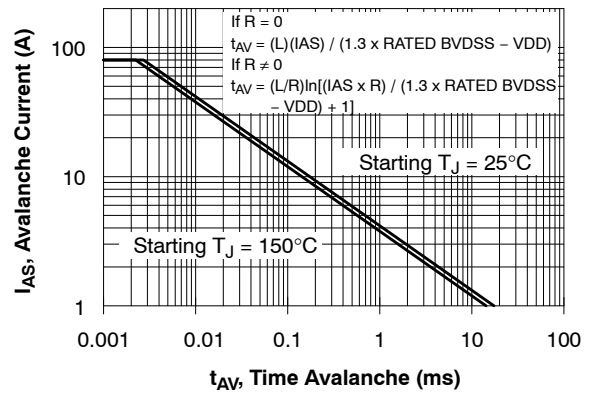


Figure 6. Unclamped Inductive Switching Capability

NOTE: Refer to On Semiconductor Application Notes AN7514 and AN7515

TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

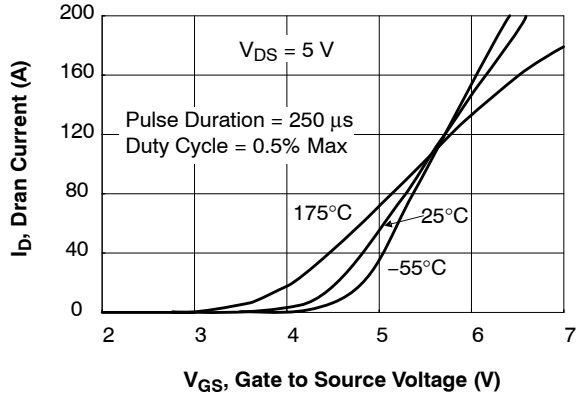


Figure 7. Transfer Characteristic

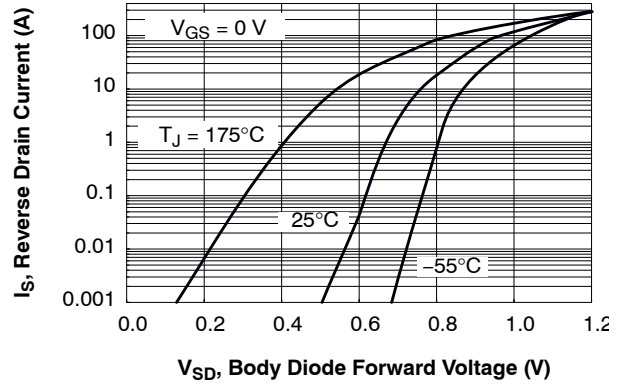


Figure 8. Forward Diode Characteristics

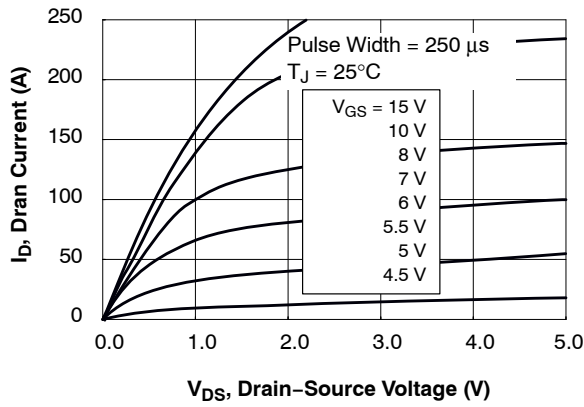


Figure 9.

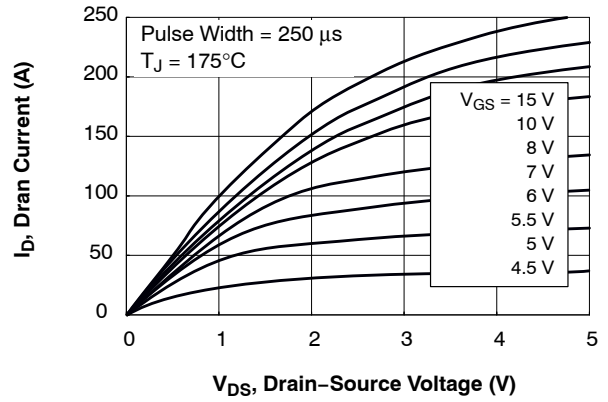


Figure 10. Peak Current Capability

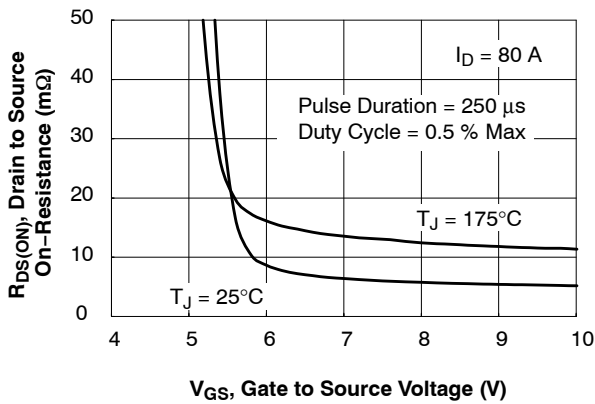


Figure 11. $R_{DS(on)}$ vs. Gate Voltage

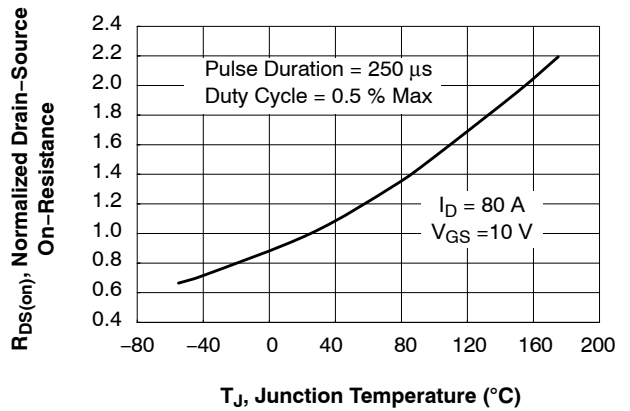


Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

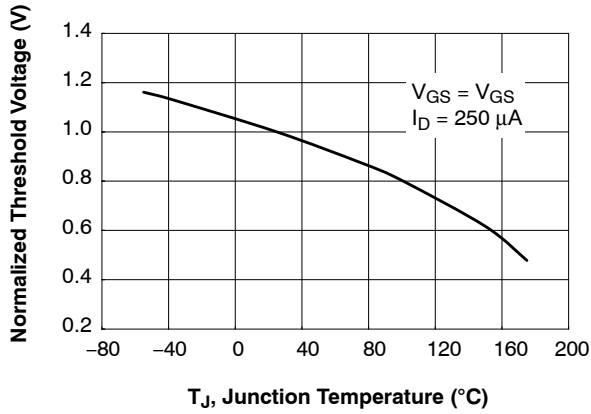


Figure 13. Normalized Gate Threshold Voltage vs. Temperature

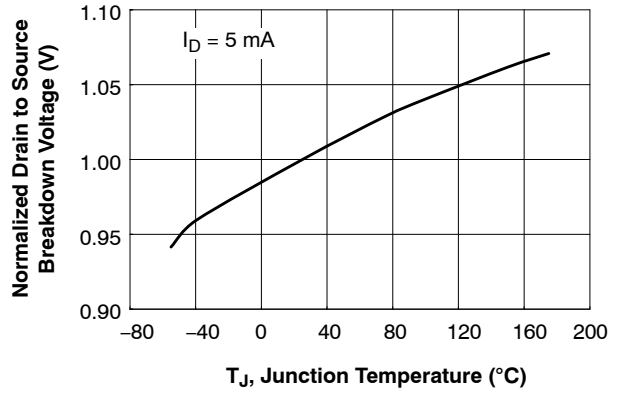


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

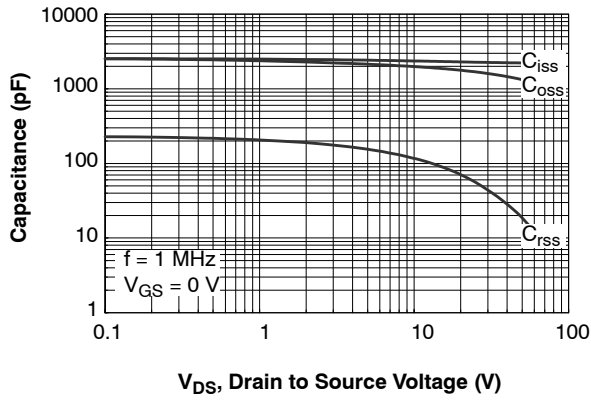


Figure 15. Capacitance vs. Drain to Source Voltage

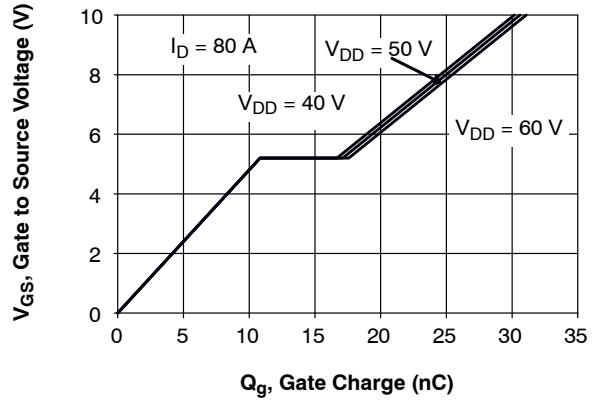


Figure 16. Gate Charge vs. Gate to Source Voltage

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